

Soon-Ku Hong

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

159
papers

3,973
citations

33
h-index

58
g-index

166
ext. papers

4,213
ext. citations

2.8
avg, IF

4.97
L-index

#	Paper	IF	Citations
159	Systematic Investigation of Growth and Properties of Ga ₂ O ₃ Films on C-Plane Sapphire Substrates Prepared by Plasma-Assisted Molecular Beam Epitaxy. <i>ECS Journal of Solid State Science and Technology</i> , 2022 , 11, 035008	2	0
158	Reduction of dislocations in GaO epilayers grown by halide vapor-phase epitaxy on a conical frustum-patterned sapphire substrate. <i>IUCrJ</i> , 2021 , 8, 462-467	4.7	6
157	Highly Asymmetric Optical Properties of Ga ₂ O ₃ as Probed by Linear and Nonlinear Optical Excitation Spectroscopy. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 1432-1440	3.8	10
156	Strengthening and fracture of deformation-processed dual fcc-phase CoCrFeCuNi and CoCrFeCu _{1.71} Ni high entropy alloys. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2020 , 781, 139241	5.3	14
155	Investigation of defect structure in homoepitaxial (2001) Ga ₂ O ₃ layers prepared by plasma-assisted molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2020 , 834, 155027	5.7	13
154	Effects of nanoepitaxial lateral overgrowth on growth of Ga ₂ O ₃ by halide vapor phase epitaxy. <i>Applied Physics Letters</i> , 2019 , 115, 091605	3.4	12
153	Precipitation and decomposition in CoCrFeMnNi high entropy alloy at intermediate temperatures under creep conditions. <i>Materialia</i> , 2019 , 8, 100445	3.2	15
152	Growth and characterization of gallium oxide films grown with nitrogen by plasma-assisted molecular-beam epitaxy. <i>Thin Solid Films</i> , 2019 , 682, 93-98	2.2	13
151	Growth of single crystal non-polar (1120) ZnSnN ₂ films on sapphire substrate. <i>Applied Surface Science</i> , 2019 , 481, 819-824	6.7	4
150	Nanoscale modulated structures by balanced distribution of atoms and mechanical/structural stabilities in CoCuFeMnNi high entropy alloys. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2019 , 762, 138120	5.3	21
149	Effect of in situ annealing on the structural properties of Bi ₂ Te ₃ films grown on (0 0 0 1) sapphire. <i>Journal of Crystal Growth</i> , 2019 , 525, 125191	1.6	
148	Effects of Growth Rate and III/V Ratio on Properties of AlN Films Grown on c-Plane Sapphire Substrates by Plasma-Assisted Molecular Beam Epitaxy. <i>Korean Journal of Materials Research</i> , 2019 , 29, 579-585	0.2	1
147	Epitaxial Growth of Bandgap Tunable ZnSnN ₂ Films on (0001) Al ₂ O ₃ Substrates by Using a ZnO Buffer. <i>Crystal Growth and Design</i> , 2018 , 18, 1385-1393	3.5	12
146	Microstructural Investigation of CoCrFeMnNi High Entropy Alloy Oxynitride Films Prepared by Sputtering Using an Air Gas. <i>Metals and Materials International</i> , 2018 , 24, 1285-1292	2.4	8
145	Structural Characterization of CoCrFeMnNi High Entropy Alloy Oxynitride Thin Film Grown by Sputtering. <i>Korean Journal of Materials Research</i> , 2018 , 28, 595-600	0.2	1
144	In Situ Oxidation of GaN Layer and Its Effect on Structural Properties of Ga ₂ O ₃ Films Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Journal of Electronic Materials</i> , 2017 , 46, 3499-3506	1.9	4
143	Depth dependent strain analysis in GaN-based light emitting diodes using surface-plasmon enhanced Raman spectroscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600805	1.6	4

142	Simultaneous determination of defect distributions and energies near InGaN/GaN quantum wells by capacitance-voltage measurement. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 39LT03	3	1
141	Thermally activated deformation and the rate controlling mechanism in CoCrFeMnNi high entropy alloy. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2017 , 682, 569-576	5.3	68
140	Co ₃ O ₄ @WCNT composites for H ₂ S gas sensor application. <i>Sensors and Actuators B: Chemical</i> , 2016 , 222, 166-172	8.5	60
139	Effects of growth pressure on morphology of ZnO nanostructures by chemical vapor transport. <i>Chemical Physics Letters</i> , 2016 , 658, 182-187	2.5	11
138	Strain mapping in a nanoscale-triangular SiGe pattern by dark-field electron holography with medium magnification mode. <i>Microscopy (Oxford, England)</i> , 2016 , 65, 499-507	1.3	1
137	Three-Dimensional Hierarchical Structures of TiO ₂ /CdS Branched Core-Shell Nanorods as a High-Performance Photoelectrochemical Cell Electrode for Hydrogen Production. <i>Journal of the Electrochemical Society</i> , 2016 , 163, H434-H439	3.9	17
136	Comprehensive Study of the Surface Morphology Evolution Induced by Thermal Annealing in A-Plane ZnO Films on R-Plane Al ₂ O ₃ Substrates. <i>Science of Advanced Materials</i> , 2016 , 8, 358-362	2.3	2
135	Characterization of Basal Plane Dislocations in PVT-Grown SiC by Transmission Electron Microscopy. <i>Korean Journal of Materials Research</i> , 2016 , 26, 656-661	0.2	
134	Fabrication and Photoelectrochemical Properties of a Cu ₂ O/CuO Heterojunction Photoelectrode for Hydrogen Production from Solar Water Splitting. <i>Korean Journal of Materials Research</i> , 2016 , 26, 604-610	0.2	2
133	High Temperature Behavior of Injection and Radiative Efficiencies and Its Effects on the Efficiency Droop in InGaN/GaN Light Emitting Diodes. <i>Journal of Nanoscience and Nanotechnology</i> , 2016 , 16, 11640-11644	1.3	2
132	A Hydrogen Sulfide Gas Sensor Based on Pd-Decorated ZnO Nanorods. <i>Journal of Nanoscience and Nanotechnology</i> , 2016 , 16, 10351-10355	1.3	12
131	Investigation of the photoelectrochemical properties for typical ZnO nanostructures grown by using chemical vapor transport. <i>Journal of the Korean Physical Society</i> , 2015 , 66, 832-838	0.6	2
130	Growth and characterization of Mg x Zn 1 - x O films grown on r-plane sapphire substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2015 , 623, 1-6	5.7	4
129	2D strain measurement in sub-10nm SiGe layer with dark-field electron holography. <i>Current Applied Physics</i> , 2015 , 15, 1529-1533	2.6	1
128	Effect of indium concentration on morphology of ZnO nanostructures grown by using CVD method and their application for H ₂ gas sensing. <i>Superlattices and Microstructures</i> , 2015 , 82, 349-356	2.8	11
127	Photoelectrochemical water splitting properties of hydrothermally-grown ZnO nanorods with controlled diameters. <i>Electronic Materials Letters</i> , 2015 , 11, 65-72	2.9	23
126	Comprehensive Structural Characterization of Commercial Blue Light Emitting Diode by Using High-Angle Annular Dark Filed Scanning Transmission Electron Microscopy and Transmission Electron Microscopy. <i>Korean Journal of Materials Research</i> , 2015 , 25, 1-8	0.2	
125	Experimental verification of effects of barrier dopings on the internal electric fields and the band structure in InGaN/GaN light emitting diodes. <i>Applied Physics Letters</i> , 2014 , 104, 121114	3.4	8

124	Crystal orientation variation of nonpolar AlN films with III/V ratio on r-plane sapphire substrates by plasma-assisted molecular beam epitaxy. <i>Electronic Materials Letters</i> , 2014 , 10, 1109-1114	2.9	2
123	Effect of First-Stage Growth Manipulation and Polarity of SiC Substrates on AlN Epilayers Grown Using Plasma-Assisted Molecular Beam Epitaxy. <i>Korean Journal of Materials Research</i> , 2014 , 24, 266-270	0.2	1
122	Growth and structural characterization of InGaN layers with controlled In content prepared by plasma-assisted molecular beam epitaxy. <i>Thin Solid Films</i> , 2013 , 546, 42-47	2.2	2
121	Microstructural characterization of high indium-composition In _x Ga _{1-x} N epilayers grown on c-plane sapphire substrates. <i>Microscopy and Microanalysis</i> , 2013 , 19 Suppl 5, 145-8	0.5	3
120	Comprehensive Study about the Effect of Heat Treatment on the Electrical Properties of Single-Crystalline ZnO Materials. <i>Applied Physics Express</i> , 2012 , 5, 075801	2.4	3
119	Realization of an open space ensemble for nanowires: a strategy for the maximum response in resistive sensors. <i>Journal of Materials Chemistry</i> , 2012 , 22, 6716		59
118	Comprehensive study of the surface morphology evolution induced by thermal annealing in single-crystalline ZnO Films and ZnO bulks. <i>Journal of the Korean Physical Society</i> , 2012 , 61, 1732-1736	0.6	3
117	Improvement of Light Extraction Efficiency and Reduction of Leakage Current in GaN-Based LED Via V-Pit Formation. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 449-451	2.2	23
116	Optimization of a zinc oxide urchin-like structure for high-performance gas sensing. <i>Journal of Materials Chemistry</i> , 2012 , 22, 1127-1134		67
115	Transparent nanoscale floating gate memory using self-assembled bismuth nanocrystals in Bi ₂ Mg _{2/3} Nb _{4/3} O ₇ (BMN) pyrochlore thin films grown at room temperature. <i>Advanced Materials</i> , 2012 , 24, 3396-400	2.4	4
114	Heteroepitaxial growth of GaN on various powder compounds (AlN, LaN, TiN, NbN, ZrN, ZrB ₂ , VN, BeO) by hydride vapor phase epitaxy. <i>Electronic Materials Letters</i> , 2012 , 8, 135-139	2.9	5
113	Surface Polarity Effects on the Hydride Vapor Phase Epitaxial Growth of GaN on 6H-SiC with a Chrome Nitride Buffer Layer. <i>Electrochemical and Solid-State Letters</i> , 2012 , 15, H148		2
112	Hydrothermal synthesis of ZnO nanorods in the presence of a surfactant. <i>Journal of Nanoscience and Nanotechnology</i> , 2012 , 12, 1328-31	1.3	2
111	Well-to-well non-uniformity in InGaN/GaN multiple quantum wells characterized by capacitance-voltage measurement with additional laser illumination. <i>Applied Physics Letters</i> , 2012 , 100, 071910	3.4	26
110	Tin oxide-carbon nanotube composite for NO _x sensing. <i>Journal of Nanoscience and Nanotechnology</i> , 2012 , 12, 1425-8	1.3	19
109	Lattice Deformation in a-Plane ZnO Films Grown on r-Plane Al ₂ O ₃ Substrates Grown by Plasma-Assisted Molecular-Beam Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 081101	2.4	5
108	Plasma-Assisted Molecular Beam Epitaxy of In _x Ga _{1-x} N Films on C-plane Sapphire Substrates. <i>Korean Journal of Materials Research</i> , 2012 , 22, 185-189	0.2	
107	Growth Characteristics of AlN by Plasma-Assisted Molecular Beam Epitaxy with Different Al Flux. <i>Korean Journal of Materials Research</i> , 2012 , 22, 539-544	0.2	

106	A simple fabrication method of randomly oriented polycrystalline zinc oxide nanowires and their application to gas sensing. <i>Advances in Natural Sciences: Nanoscience and Nanotechnology</i> , 2011 , 2, 015002	1.6	5
105	Growth and optical properties of ZnO nanorods prepared through hydrothermal growth followed by chemical vapor deposition. <i>Journal of Alloys and Compounds</i> , 2011 , 509, 5137-5141	5.7	30
104	Polyaniline-chitosan nanocomposite: High performance hydrogen sensor from new principle. <i>Sensors and Actuators B: Chemical</i> , 2011 , 160, 1020-1025	8.5	33
103	Raman and emission characteristics of a-plane InGa _{1-x} N/GaN blue-green light emitting diodes on r-sapphire substrates. <i>Journal of Applied Physics</i> , 2011 , 109, 043103-043103-4	2.5	9
102	Suppression of composition modulation in In-rich In _x Ga _{1-x} N layer with high In content (x ~ 0.67). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 2737-2740	1.6	
101	Enhanced photoelectrochemical activity of the TiO ₂ /ITO nanocomposites grown onto single-walled carbon nanotubes at a low temperature by nanocluster deposition. <i>Advanced Materials</i> , 2011 , 23, 5557-62	2.4	28
100	The thermal treatment effects of CrN buffer layer on crystal quality of Zn-polar ZnO films. <i>Thin Solid Films</i> , 2011 , 519, 3417-3420	2.2	2
99	Properties of (11 $\bar{2}$ 0) a-plane ZnO films on sapphire substrates grown at different temperatures by plasma-assisted molecular beam epitaxy. <i>Thin Solid Films</i> , 2011 , 519, 6394-6398	2.2	15
98	Effects of gallium doping on properties of a-plane ZnO films on r-plane sapphire substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2011 , 29, 03A111	2.9	3
97	Structural Characterization of Bismuth Zinc Oxide Thin Films Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Korean Journal of Materials Research</i> , 2011 , 21, 563-567	0.2	
96	Growth of Epitaxial AlN Thin Films on Sapphire Substrates by Plasma-Assisted Molecular Beam Epitaxy. <i>Korean Journal of Materials Research</i> , 2011 , 21, 634-638	0.2	2
95	Anisotropic properties of periodically polarity-inverted zinc oxide structures. <i>Journal of Applied Physics</i> , 2010 , 107, 123519	2.5	2
94	High-Quality p-Type ZnO Films Grown by Co-Doping of N and Te on Zn-Face ZnO Substrates. <i>Applied Physics Express</i> , 2010 , 3, 031103	2.4	28
93	Effects of Basal Stacking Faults on Electrical Anisotropy of Nonpolar a-Plane (11 $\bar{2}$ 0) GaN Light-Emitting Diodes on Sapphire Substrate. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 595-597	2.2	29
92	Growth and optical properties of ZnO nanorods prepared through hydrothermal growth followed by chemical vapor deposition 2010 ,		1
91	Effects of strain-control layers on piezoelectric field and indium incorporation in InGa _{1-x} N/GaN blue quantum wells. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 221-223	2.5	6
90	Interface and defect structures in ZnO films on m-plane sapphire substrates. <i>Journal of Crystal Growth</i> , 2010 , 312, 238-244	1.6	28
89	Growth of epitaxial ZnO films on Si (1 1 1) substrates with Cr compound buffer layer by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2010 , 312, 2190-2195	1.6	3

88	Investigation of nonpolar (112̄0) a-plane ZnO films grown under various Zn/O ratios by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2010 , 312, 2196-2200	1.6	22
87	Investigation of initial growth and very thin () ZnO films by cross-sectional and plan-view transmission electron microscopy. <i>Applied Surface Science</i> , 2010 , 256, 1849-1854	6.7	7
86	Microstructural investigation of ZnO films grown on (111) Si substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2010 , 312, 1557-1562	1.6	5
85	Effects of low temperature ZnO and MgO buffer thicknesses on properties of ZnO films grown on (0001) Al ₂ O ₃ substrates by plasma-assisted molecular beam epitaxy. <i>Thin Solid Films</i> , 2010 , 519, 223-227 ^{2,2}	2.2	12
84	Synthesis of porous CuO nanowires and its application to hydrogen detection. <i>Sensors and Actuators B: Chemical</i> , 2010 , 146, 266-272	8.5	126
83	Nanocomposite of cobalt oxide nanocrystals and single-walled carbon nanotubes for a gas sensor application. <i>Sensors and Actuators B: Chemical</i> , 2010 , 150, 160-166	8.5	55
82	Enhancement of CO gas sensing properties in ZnO thin films deposited on self-assembled Au nanodots. <i>Sensors and Actuators B: Chemical</i> , 2010 , 151, 127-132	8.5	44
81	Origin of second-order nonlinear optical response of polarity-controlled ZnO films. <i>Applied Physics Letters</i> , 2009 , 94, 231118	3.4	15
80	Structural and optical investigations of periodically polarity inverted ZnO heterostructures on (0001) Al ₂ O ₃ . <i>Applied Physics Letters</i> , 2009 , 94, 141904	3.4	10
79	Synthesis and hydrogen gas sensing properties of ZnO wirelike thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2009 , 27, 1347-1351	2.9	31
78	Spontaneous transition in preferred orientation of GaN domains grown on r-plane sapphire substrate from [112̄0] to [0001]. <i>Applied Physics Letters</i> , 2009 , 94, 102103	3.4	5
77	ZnO nanowires prepared by hydrothermal growth followed by chemical vapor deposition for gas sensors. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1667		17
76	Effects of two-step growth by employing Zn-rich and O-rich growth conditions on properties of (112̄0) ZnO films grown by plasma-assisted molecular beam epitaxy on sapphire. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1635		6
75	Lateral arrays of vertical ZnO nanowalls on a periodically polarity-inverted ZnO template. <i>Nanotechnology</i> , 2009 , 20, 235304	3.4	5
74	Dynamic Characteristics of Metal-Induced Laterally Crystallized Polycrystalline Silicon Thin-Film Transistor Devices and Circuits Fabricated with Asymmetric Precrystallization. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 020205	1.4	2
73	Growth and structural properties of ZnO films on (10̄10) m-plane sapphire substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1625		20
72	Ultrastructural observation of electron irradiation damage of lamellar bone. <i>Journal of Materials Science: Materials in Medicine</i> , 2009 , 20, 959-65	4.5	8
71	Nanostructural analysis of trabecular bone. <i>Journal of Materials Science: Materials in Medicine</i> , 2009 , 20, 1419-26	4.5	23

70	Electrical and magnetic properties of Mn-doped Si thin films. <i>Physica B: Condensed Matter</i> , 2009 , 404, 1686-1688	2.8	6
69	Hydride vapor phase epitaxy of GaN on the vicinal c-sapphire with a CrN interlayer. <i>Journal of Crystal Growth</i> , 2009 , 311, 470-473	1.6	3
68	Microstructural Analysis of Void Formation Due to a NH ₄ Cl Layer for Self-Separation of GaN Thick Films. <i>Crystal Growth and Design</i> , 2009 , 9, 2877-2880	3.5	5
67	Structural and stimulated emission characteristics of diameter-controlled ZnO nanowires using buffer structure. <i>Journal Physics D: Applied Physics</i> , 2009 , 42, 225403	3	4
66	Reduction of dislocations in GaN films on AlN/sapphire templates using CrN nanoislands. <i>Applied Physics Letters</i> , 2008 , 92, 091906	3.4	21
65	Anisotropic optical properties of free and bound excitons in highly strained A-plane ZnO investigated with polarized photoreflectance and photoluminescence spectroscopy. <i>Applied Physics Letters</i> , 2008 , 92, 201907	3.4	30
64	Growth and structural properties of m-plane ZnO on MgO (001) by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2008 , 92, 233505	3.4	50
63	Growth of Polarity-Controlled ZnO Films on (0001) Al ₂ O ₃ . <i>Journal of Electronic Materials</i> , 2008 , 37, 736-743	3.4	13
62	Strong enhancement of emissions from nanostructured ZnO thin films grown by plasma-assisted molecular-beam epitaxy on nanopored Si(001) substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 1598-1601	1.6	
61	The roles of low-temperature buffer layer for thick GaN growth on sapphire. <i>Journal of Crystal Growth</i> , 2008 , 310, 920-923	1.6	4
60	Effects of Zn pre-exposure temperature on the microstructures of ZnO films grown on Si(001) substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2008 , 310, 1118-1123	1.6	6
59	Characterization of microstructure and defects in epitaxial ZnO (112̄0) films on Al ₂ O ₃ (11̄02) substrates by transmission electron microscopy. <i>Journal of Crystal Growth</i> , 2008 , 310, 4102-4109	1.6	26
58	Dynamic Characteristics of Multi-Channel Metal-Induced Unilaterally Precrystallized Polycrystalline Silicon Thin-Film Transistor Devices and Circuits. <i>Korean Journal of Materials Research</i> , 2008 , 18, 507-510	0.2	2
57	Growth and Characterization of Zinc-Oxide Films Grown by Using Plasma-Assisted Molecular Beam Epitaxy on (111) Silicon Substrates with Ti and Titanium Compound Buffer Layers. <i>Journal of the Korean Physical Society</i> , 2008 , 53, 276-281	0.6	8
56	Temperature and Polarization Dependence of the Near-Band-Edge Photoluminescence in a Non-Polar ZnO Film Grown by Using Molecular Beam Epitaxy. <i>Journal of the Korean Physical Society</i> , 2008 , 53, 288-291	0.6	3
55	Growth and Characterization of Zinc Oxide Nanostructures on (111) Silicon Substrates with Aluminum Compound Layer. <i>Journal of the Korean Physical Society</i> , 2008 , 53, 292-298	0.6	7
54	Structural investigation of nitrided c-sapphire substrate by grazing incidence x-ray diffraction and transmission electron microscopy. <i>Applied Physics Letters</i> , 2007 , 91, 202116	3.4	7
53	Structural and optical properties of non-polar A-plane ZnO films grown on R-plane sapphire substrates by plasma-assisted molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , 2007 , 309, 121-127	1.6	85

52	Self-separated freestanding GaN using a NH ₄ Cl interlayer. <i>Applied Physics Letters</i> , 2007 , 91, 192108	3.4	20
51	Polarity control of ZnO films on (0001) Al ₂ O ₃ by Cr-compound intermediate layers. <i>Applied Physics Letters</i> , 2007 , 90, 201907	3.4	44
50	The Growth of ZnO on CrN Buffer Layer Using Surface Phase Control by Plasma Assisted Molecular-beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 957, 1		
49	Origin of forward leakage current in GaN-based light-emitting devices. <i>Applied Physics Letters</i> , 2006 , 89, 132117	3.4	128
48	Slowdown in development of self-assembled InAs/GaAs(001) dots near the critical thickness. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 1886		3
47	Control of the ZnO nanowires nucleation site using microfluidic channels. <i>Journal of Physical Chemistry B</i> , 2006 , 110, 3856-9	3.4	37
46	Magnetic and electrical properties of MBE-grown (Ge _{1-x} Si _x) _{1-y} Mny thin films. <i>Current Applied Physics</i> , 2006 , 6, 478-481	2.6	11
45	Magneto-transport properties of amorphous Ge _{1-x} Mnx thin films. <i>Current Applied Physics</i> , 2006 , 6, 545-548		13
44	Growth and magnetism in amorphous Si _{1-x} Mnx thin films grown by thermal deposition. <i>Journal of Magnetism and Magnetic Materials</i> , 2006 , 304, e167-e169	2.8	5
43	Observation of ferromagnetism and anomalous Hall effect in laser-deposited chromium-doped indium tin oxide films. <i>Solid State Communications</i> , 2006 , 137, 41-43	1.6	36
42	Control of crystal polarity in oxide and nitride semiconductors by interface engineering. <i>Journal of Electroceramics</i> , 2006 , 17, 255-261	1.5	7
41	Structural and Optical Properties of ZnO Thin Films Grown on SiO ₂ /Si(100) Substrates by RF Magnetron Sputtering. <i>Korean Journal of Materials Research</i> , 2006 , 16, 360-366	0.2	1
40	ZnO epitaxial layers grown on c-sapphire substrate with MgO buffer by plasma-assisted molecular beam epitaxy (P-MBE). <i>Semiconductor Science and Technology</i> , 2005 , 20, S13-S21	1.8	58
39	Nanostructure formation and emission characterization of blue emission InN/GaN quantum well with thin InN well layers. <i>Journal of Crystal Growth</i> , 2005 , 281, 349-354	1.6	14
38	Ferromagnetism and Anomalous Hall Effect in p-Zn _{0.99} Mn _{0.01} O:P. <i>Journal of Magnetism</i> , 2005 , 10, 95-98	1.9	5
37	Influence of growth flux and surface supersaturation on InGaAs/GaAs strain relaxation. <i>Applied Physics Letters</i> , 2004 , 84, 1085-1087	3.4	5
36	Doping effects in ZnO layers using Li ₃ N as a doping source. <i>Journal of Crystal Growth</i> , 2003 , 251, 628-632	1.6	9
35	Study on MgO buffer in ZnO layers grown by plasma-assisted molecular beam epitaxy on Al ₂ O ₃ (0001). <i>Thin Solid Films</i> , 2003 , 445, 213-218	2.2	23

34	Nanoheteroepitaxy of GaN on a nanopore array Si surface. <i>Applied Physics Letters</i> , 2003 , 83, 1752-1754	3.4	60
33	Interface Engineering in ZnO Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 229, 803-813	1.3	10
32	Control of polarity of heteroepitaxial ZnO films by interface engineering. <i>Applied Surface Science</i> , 2002 , 190, 491-497	6.7	20
31	A challenge in molecular beam epitaxy of ZnO: control of material properties by interface engineering. <i>Thin Solid Films</i> , 2002 , 409, 153-160	2.2	34
30	Improvement in crystallinity of ZnSe by inserting a low-temperature buffer layer between the ZnSe epilayer and the GaAs substrate. <i>Journal of Crystal Growth</i> , 2002 , 242, 95-103	1.6	20
29	Correlation of surface chemistry of GaAs substrates with growth mode and stacking fault density in ZnSe epilayers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2002 , 20, 1948	2.9	2
28	Control of ZnO film polarity. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002 , 20, 1656		17
27	Control of crystal polarity in a wurtzite crystal: ZnO films grown by plasma-assisted molecular-beam epitaxy on GaN. <i>Physical Review B</i> , 2002 , 65,	3.3	94
26	Morphology evolution of ZnO(000 1) surface during plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2002 , 80, 1358-1360	3.4	51
25	Investigation of ZnO epilayers grown under various Zn/O ratios by plasma-assisted molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2002 , 92, 4354-4360	2.5	112
24	ZnO and related materials: Plasma-Assisted molecular beam epitaxial growth, characterization and application. <i>Journal of Electronic Materials</i> , 2001 , 30, 647-658	1.9	28
23	ZnO epilayers on GaN templates: Polarity control and valence-band offset. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001 , 19, 1429		28
22	Structural characteristics and magnetic properties of EMnO2 films grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2001 , 90, 351-354	2.5	18
21	Stimulated emission and optical gain in ZnO epilayers grown by plasma-assisted molecular-beam epitaxy with buffers. <i>Applied Physics Letters</i> , 2001 , 78, 1469-1471	3.4	159
20	Effects of an extremely thin buffer on heteroepitaxy with large lattice mismatch. <i>Applied Physics Letters</i> , 2001 , 78, 3352-3354	3.4	84
19	Band alignment at a ZnO/GaN (0001) heterointerface. <i>Applied Physics Letters</i> , 2001 , 78, 3349-3351	3.4	114
18	Low stacking-fault density in ZnSe epilayers directly grown on epi-ready GaAs substrates without GaAs buffer layers. <i>Applied Physics Letters</i> , 2001 , 78, 165-167	3.4	46
17	Evolution of initial layers of plasma-assisted MBE grown ZnO on (0001)GaN/sapphire. <i>Journal of Crystal Growth</i> , 2000 , 214-215, 81-86	1.6	27

16	Two-dimensional growth of ZnO films on sapphire(0001) with buffer layers. <i>Journal of Crystal Growth</i> , 2000 , 214-215, 87-91	1.6	40
15	Defect characterization in epitaxial ZnO/epi-GaN/Al ₂ O ₃ heterostructures: transmission electron microscopy and triple-axis X-ray diffractometry. <i>Journal of Crystal Growth</i> , 2000 , 209, 537-541	1.6	46
14	Formation and properties of self-organized III-V quantum islands. <i>Thin Solid Films</i> , 2000 , 367, 68-74	2.2	49
13	Characterization of ZnSe/ZnMgBeSe single quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 576-580	3	3
12	Control and characterization of ZnO/GaN heterointerfaces in plasma-assisted MBE-grown ZnO films on GaN/Al ₂ O ₃ . <i>Applied Surface Science</i> , 2000 , 159-160, 441-448	6.7	28
11	Plasma-assisted molecular beam epitaxy for ZnO based III-V semiconductor oxides and their heterostructures. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 1514		30
10	Control of polarity of ZnO films grown by plasma-assisted molecular-beam epitaxy: Zn- and O-polar ZnO films on Ga-polar GaN templates. <i>Applied Physics Letters</i> , 2000 , 77, 3571-3573	3.4	60
9	Plasma-assisted molecular-beam epitaxy of ZnO epilayers on atomically flat MgAl ₂ O ₄ (111) substrates. <i>Applied Physics Letters</i> , 2000 , 76, 245-247	3.4	93
8	Origin of hexagonal-shaped etch pits formed in (0001) GaN films. <i>Applied Physics Letters</i> , 2000 , 77, 82-84	3.4	91
7	Layer-by-layer growth of ZnO epilayer on Al ₂ O ₃ (0001) by using a MgO buffer layer. <i>Applied Physics Letters</i> , 2000 , 76, 559-561	3.4	242
6	Ga-doped ZnO films grown on GaN templates by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2000 , 77, 3761-3763	3.4	332
5	Non-alloyed Au/p-ZnSe/p-BeTe ohmic contact layers for ZnSe-based blue-green laser diodes. <i>Electronics Letters</i> , 1999 , 35, 1740	1.1	2
4	Evaluation of nanopipes in MOCVD grown (0001) GaN/Al ₂ O ₃ by wet chemical etching. <i>Journal of Crystal Growth</i> , 1998 , 191, 275-278	1.6	53
3	Determination of defect types of ZnSe-based epilayers by etch-pit configurations. <i>Journal of Crystal Growth</i> , 1997 , 181, 343-350	1.6	3
2	Influence of sputtering pressure on the microstructure evolution of AlN thin films prepared by reactive sputtering. <i>Thin Solid Films</i> , 1995 , 261, 148-153	2.2	40
1	Microstructural degradation during Zn diffusion in a GaInAsP/InP heterostructure: Layer mixing, misfit dislocation generation, and Zn ₃ P ₂ precipitation. <i>Journal of Applied Physics</i> , 1992 , 72, 4063-4072	2.5	11